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Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 12406-018001	Application No.
Information Disclosure Statement by Applicant (Use several sheets if necessary) (37 CFR §1.98(b))		Applicant: Martin Behringer et al.	
		Filing Date: Herewith	Group Art Unit

U.S. Patent Documents

Examiner Initial	Desig. ID	Patent Number	Issue Date	Patentee	Class	Subclass	Filing Date If Appropriate
SR	AA	5,396,103	03/07/1995	OIU et al.			
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						

Foreign Patent Documents or Published Foreign Patent Applications

Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation Yes	Translation No
	AJ							
	AK							
	AL							
	AM							
	AN							

Other Documents (include Author, Title, Date, and Place of Publication)

Examiner Initial	Desig. ID	Document
SR	AO	Magnea, N., "ZnTe fractional monolayers and dots in a CdTe matrix" 6th International Conference on II-VI Compounds and related optoelectric materials, Journal of Crystal Growth, 138 (1994): 550-558.
SR	AP	Kutzer, V. et al., "Gain to absorption conversion by increasing excitation density in excitonic waveguides", Journal of Crystal Growth, 184/185 (1998): 632-636.
SR	AQ	Faschinger, W. et al., "Processes occurring during the formation of graded ZnSe/ZnTe contacts on p-ZnSe", Semicond. Sci. Technol., 12 (1997): 1291-1297.
SR	AR	Hirose, J. et al., "p-type conductivity control of ZnSe with insertion of ZnTe:Li submonolayers in metalorganic molecular-beam epitaxy", Journal of Applied Physics, 84 (01 DEC 1998): 6100-6104.
SR	AS	Fan, Y. et al., "Graded band gap ohmic contact to p-ZnSe", Applied Physics Letter, 61 (26), 28 DEC 1992: 3160-3162.

Examiner Signature	Date Considered
Shamim Ahmed	2/1/05

EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.